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Growth and oxygen doping of thin film FeTe by Molecular Beam Epitaxy<sup>1</sup> MAO ZHENG, CAN ZHANG, HEFEI HU, JIAN-MIN ZUO, JAMES ECKSTEIN, University of Illinis Urbana-Champaign — FeTe is isomorphic to FeSe, a representative of the 11 family of iron based superconductors. While not a superconductor itself, FeTe, particularly in thin film form, undergoes a superconducting transition when doped with oxygen. In this presentation, we will discuss the growth of FeTe by MBE and various schemes we used to dope the samples. Evidence from our investigation suggests that FeTe films are doped via an oxygen diffusion process which is strongly activated by temperature.

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